

Electronic Supplementary Information

Enhanced thermoelectric transport properties of *n*-type InSe due to emergence of flat band by Si doping

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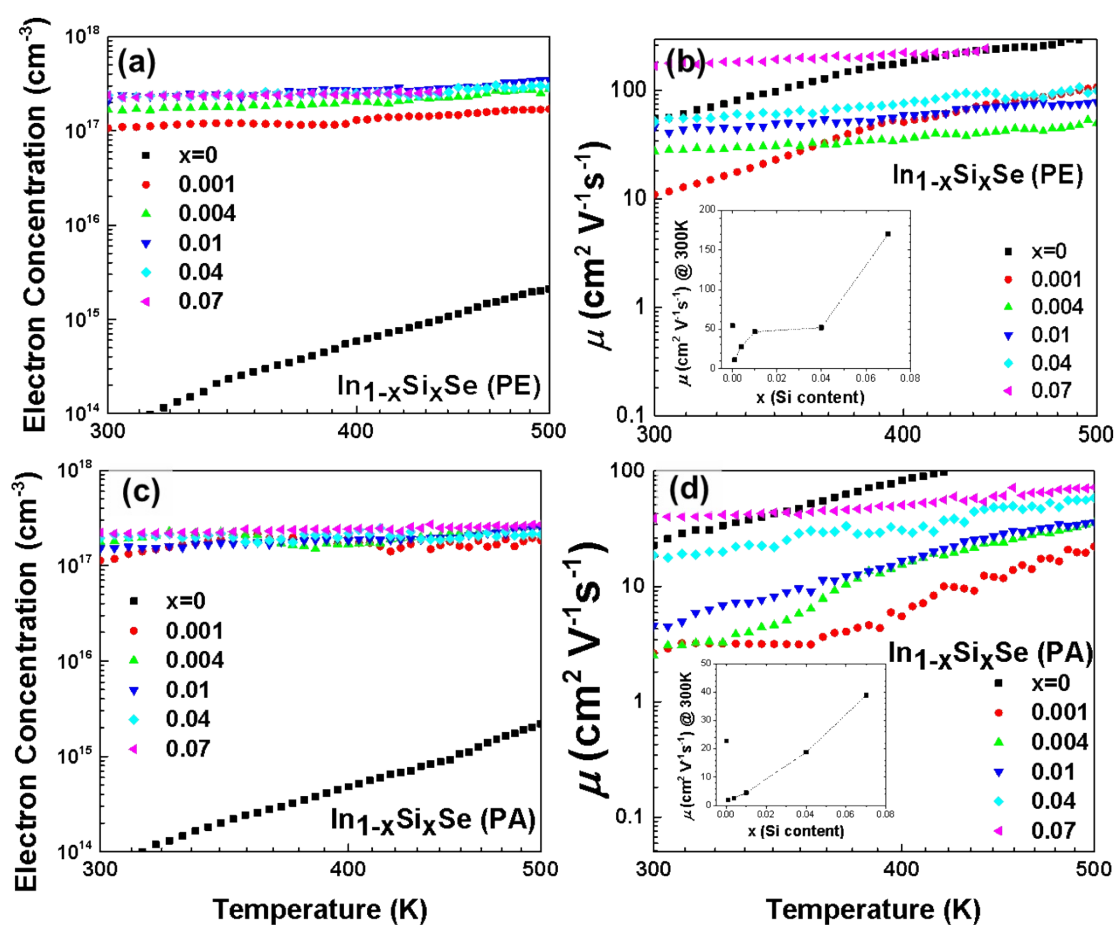


Figure S1. Carrier concentration and mobility in the range of 300 to 500 K in the PE and PA directions with respect to the pressing direction.